## Hiroshi Uchida

List of Publications by Year in descending order

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279798 265206 2,478 171 23 42 citations h-index g-index papers 174 174 174 2141 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Lower-temperature processing of potassium niobate films by microwave-assisted hydrothermal deposition technique. Journal of the Ceramic Society of Japan, 2022, 130, 123-130.	1.1	1
2	Synthesis and Antioxidant Activity of Silver Nanoparticles Using the Odontonema strictum Leaf Extract. Molecules, 2022, 27, 3210.	3.8	7
3	One-axis-oriented growth of PZT thin films on transparent glass substrates using metal oxide nanosheets. Japanese Journal of Applied Physics, 2022, 61, SN1006.	1.5	1
4	Origin of Grain Size Effects on Voltageâ€Driven Ferroelastic Domain Evolution in Polycrystalline Tetragonal Lead Zirconate Titanate Thin Film. Advanced Functional Materials, 2020, 30, 1909100.	14.9	7
5	Epitaxial growth of Mg <sub>2</sub> Si films on (111) Si substrates covered with epitaxial SiC layers. Japanese Journal of Applied Physics, 2020, 59, SF1001.	1.5	4
6	Good piezoelectricity of self-polarized thick epitaxial (K,Na)NbO3 films grown below the Curie temperature (240 °C) using a hydrothermal method. Applied Physics Letters, 2020, 117, .	3.3	8
7	Barkhausen noise analysis of thin film ferroelectrics. Applied Physics Letters, 2020, 117, 012902.	3.3	4
8	Composition Dependence of Crystal Structures and Electrical Properties of Ca-Mg-Si Films Prepared by Sputtering. Journal of Electronic Materials, 2020, 49, 7509-7517.	2.2	1
9	Role of alkan-1-ol solvents in the synthesis of yellow luminescent carbon quantum dots (CQDs): van der Waals force-caused aggregation and agglomeration. RSC Advances, 2020, 10, 14396-14402.	3.6	7
10	Room-temperature deposition of ferroelectric HfO2-based films by the sputtering method. Applied Physics Letters, 2020, $116$ , .	3.3	28
11	High yield preparation of (100) <i><sub>c</sub></i> -oriented (K,Na)NbO <sub>3</sub> thick films by hydrothermal method using amorphous niobium source. Journal of the Ceramic Society of Japan, 2020, 128, 512-517.	1.1	9
12	Rapid deposition of (K,Na)NbO3 thick films using microwave-assisted hydrothermal technique. Japanese Journal of Applied Physics, 2020, 59, SPPBO2.	1.5	7
13	Effect of Ta-substitution on the deposition of (K,Na)(Nb,Ta)O3 films by hydrothermal method. Japanese Journal of Applied Physics, 2019, 58, SLLB12.	1.5	8
14	Growth of epitaxial (K, Na)NbO3 films with various orientations by hydrothermal method and their properties. Japanese Journal of Applied Physics, 2019, 58, SLLB14.	1.5	11
15	Effects of starting materials on the deposition behavior of hydrothermally synthesized {1 0 0} -oriented epitaxial (K,Na)NbO3 thick films and their ferroelectric and piezoelectric properties. Journal of Crystal Growth, 2019, 511, 1-7.	1.5	18
16	Kinetics of interfacial microstructural variation across insulator-thermoelectric semiconductor interface and its effects on thermoelectric properties of magnesium silicide thin films. Materialia, 2019, 7, 100375.	2.7	0
17	Preparation of CaMgSi and Ca7Mg7.25Si14 single phase films and their thermoelectric properties. MRS Advances, 2019, 4, 1503-1508.	0.9	3
18	Deposition of orientation-controlled thick (K,Na)NbO <sub>3</sub> films on metal substrates by repeated hydrothermal deposition technique. Journal of the Ceramic Society of Japan, 2019, 127, 478-484.	1.1	7

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19	Low-temperature deposition of Li substituted (K,Na)NbO <sub>3</sub> films by a hydrothermal method and their structural and ferroelectric properties. Journal of the Ceramic Society of Japan, 2019, 127, 388-393.	1.1	8
20	Control of p- and n-type Conduction in Thermoelectric Non-doped Mg2Si Thin Films Prepared by Sputtering Method. MRS Advances, 2018, 3, 1355-1359.	0.9	5
21	Epitaxial ferroelectric Y-doped HfO <sub>2</sub> film grown by the RF magnetron sputtering. Japanese Journal of Applied Physics, 2018, 57, 11UF15.	1.5	15
22	Crystallization behavior and ferroelectric property of HfO <sub>2</sub> â€"ZrO <sub>2</sub> films fabricated by chemical solution deposition. Japanese Journal of Applied Physics, 2018, 57, 11UF06.	1.5	22
23	Thickness-dependent crystal structure and electric properties of epitaxial ferroelectric Y2O3-HfO2 films. Applied Physics Letters, 2018, 113, .	3.3	48
24	Fabrication of ferroelectric Fe doped HfO <sub>2</sub> epitaxial thin films by ion-beam sputtering method and their characterization. Japanese Journal of Applied Physics, 2018, 57, 11UF02.	1.5	23
25	Preparation of {001} <sub>c</sub> -oriented epitaxial (K, Na)NbO <sub>3</sub> thick films by repeated hydrothermal deposition technique. Journal of the Ceramic Society of Japan, 2018, 126, 281-285.	1.1	10
26	Time response demonstration of in situ lattice deformation under an applied electric field by synchrotron-based time-resolved X-ray diffraction in polar-axis-oriented epitaxial Pb(Zr,Ti)O3 film. Japanese Journal of Applied Physics, 2018, 57, 0902B8.	1.5	2
27	Solid-solution thin films of ternary BaTiO3–Bi(Mg1/2Ti1/2)O3–BiFeO3 system epitaxially grown on SrRuO3//SrTiO3 substrates via chemical solution process. Japanese Journal of Applied Physics, 2018, 57, 0902B5.	1.5	1
28	Hydrothermal Deposition of KNbO <sub>3</sub> Films on Metal Substrates having Three-Dimensional Structure. Funtai Oyobi Fummatsu Yakin/Journal of the Japan Society of Powder and Powder Metallurgy, 2018, 65, 673-677.	0.2	0
29	Preparation of preferentially (111)-oriented Mg <sub>2</sub> Si thin films on (001)Al <sub>2</sub> O <sub>3</sub> and (100)CaF <sub>2</sub> substrates and their thermoelectric properties. Japanese Journal of Applied Physics, 2017, 56, 05DC02.	1.5	9
30	Crystal structure and dielectric/ferroelectric properties of CSD-derived HfO 2 -ZrO 2 solid solution films. Ceramics International, 2017, 43, S501-S505.	4.8	24
31	Probing Oxygen Vacancies in BaTiO3 Powders and Single Crystals by Micro-Raman Scattering. Advanced Structured Materials, 2017, , 65-75.	0.5	0
32	Effect of the film thickness on the crystal structure and ferroelectric properties of (Hf 0.5 Zr 0.5)O 2 thin films deposited on various substrates. Materials Science in Semiconductor Processing, 2017, 70, 239-245.	4.0	41
33	Fabrication and characterization of {110}-oriented Pb(Zr,Ti)O <sub>3</sub> thin films on Pt/SiO <sub>2</sub> /Si substrates using PdO//Pd buffer layer. Japanese Journal of Applied Physics, 2017, 56, 10PF09.	1.5	3
34	Evaluation of oxygen vacancies in ZnO single crystals and powders by micro-Raman spectroscopy. Journal of the Ceramic Society of Japan, 2017, 125, 445-448.	1.1	31
35	Characterization of (111)-oriented epitaxial (K <sub>0.5</sub> Na <sub>0.5</sub> )NbO <sub>3</sub> thick films deposited by hydrothermal method. Japanese Journal of Applied Physics, 2017, 56, 10PF04.	1.5	10
36	Influence of Internal Strains of (110)-One-Axis-Oriented (Ba0.5Sr0.5)TiO3 (BST) Thin Films on Their Dielectric Behaviors. Science of Advanced Materials, 2017, 9, 1806-1809.	0.7	1

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37	Polarization switching behavior of one-axis-oriented lead zirconate titanate films fabricated on metal oxide nanosheet layer. Japanese Journal of Applied Physics, 2017, 56, 10PF10.	1.5	2
38	Thermally stable dielectric responses in uniaxially (001)-oriented CaBi4Ti4O15 nanofilms grown on a Ca2Nb3O10â^' nanosheet seed layer. Scientific Reports, 2016, 6, 20713.	3.3	8
39	Impact of mechanical stress on ferroelectricity in (Hf0.5Zr0.5)O2 thin films. Applied Physics Letters, 2016, 108, .	3.3	187
40	Simultaneous achievement of high dielectric constant and low temperature dependence of capacitance in (111)-oriented BaTiO3-Bi(Mg0.5Ti0.5)O3-BiFeO3 solid solution thin films. AIP Advances, $2016, 6, .$	1.3	4
41	Crystal structure and compositional analysis of epitaxial (K <sub>0.56</sub> Na <sub>0.44</sub> )NbO <sub>3</sub> films prepared by hydrothermal method. Journal of Materials Research, 2016, 31, 693-701.	2.6	7
42	Angular dependence of Raman spectrum for Pb(Zr,Ti)O3epitaxial films. Japanese Journal of Applied Physics, 2016, 55, 10TC07.	1.5	4
43	Growth of (111)-oriented epitaxial and textured ferroelectric Y-doped HfO2 films for downscaled devices. Applied Physics Letters, 2016, 109, .	3.3	62
44	Orientation control and domain structure analysis of $\{100\}$ -oriented epitaxial ferroelectric orthorhombic HfO2-based thin films. Journal of Applied Physics, 2016, 119, .	2.5	57
45	Formation of $(111)$ orientation-controlled ferroelectric orthorhombic HfO2 thin films from solid phase via annealing. Applied Physics Letters, 2016, 109, .	3.3	29
46	Growth of epitaxial tetragonal (Bi,K)TiO3films and their ferroelectric and piezoelectric properties. Japanese Journal of Applied Physics, 2016, 55, 10TA13.	1.5	8
47	Chemical deposition of silica-based thin films under supercritical carbon dioxide atmosphere using tetraethylorthosilicate precursor with oxidizing agents. Journal of the Ceramic Society of Japan, 2016, 124, 18-22.	1.1	2
48	Dielectric properties of BaTiO <sub>3</sub> 4/21/21/21/20/0< films with preferential crystal orientation. Journal of the Ceramic Society of Japan, 2016, 124, 648-652.	subn≯38	.lt;/sub>
49	Facile preparation of N-doped TiO2 at ambient temperature and pressure under UV light with 4-nitrophenol as the nitrogen source and its photocatalytic activities. Photochemical and Photobiological Sciences, 2016, 15, 1061-1070.	2.9	4
50	Orientation control of barium titanate films using metal oxide nanosheet layer. Japanese Journal of Applied Physics, 2016, 55, 10TA15.	1.5	5
51	Preparation of Ca-Si Films on (001) Al2O3 Substrates by an RF Magnetron Sputtering Method and Their Electrical Properties. Journal of Electronic Materials, 2016, 45, 3121-3126.	2.2	6
52	Synthesis of TiO2 hollow particles with highly dispersed CaCO3 template particulates and their photoactivity toward a VOC pollutant. Journal of Sol-Gel Science and Technology, 2016, 78, 373-381.	2.4	5
53	Fabrication of (100) <sub>c</sub> -oriented Mn-doped bismuth ferrite films on silicon and stainless steel substrates using calcium niobate nanosheets. Journal of the Ceramic Society of Japan, 2015, 123, 322-328.	1.1	5
54	Fabrication and characterization of (110)-oriented (Ba0.5,Sr0.5)TiO3thin films using PdO//Pd buffer layer. Japanese Journal of Applied Physics, 2015, 54, 10NA15.	1.5	8

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55	Reconstruction in Atom Probe Tomography Considering the Cone Angle of Needle-Like Shaped Samples and Evaluation of Reliability. E-Journal of Surface Science and Nanotechnology, 2015, 13, 235-238.	0.4	1
56	Vibration-energy-harvesting properties of hydrothermally synthesized (K,Na)NbO3films deposited on flexible metal foil substrates. Japanese Journal of Applied Physics, 2015, 54, 10ND06.	1.5	18
57	Atom probe tomography study on Ge1â^'xâ^'ySnxCy hetero-epitaxial film on Ge substrates. Thin Solid Films, 2015, 592, 54-58.	1.8	1
58	Chemical Fluid Deposition of Hf-Zr-O-based Thin Films using Supercritical Carbon Dioxide Fluid. Materials Research Society Symposia Proceedings, 2015, 1729, 99-104.	0.1	2
59	Inhomogeneous distribution of manganese atoms in ferromagnetic ZnSnAs2:Mn thin films on InP revealed by three-dimensional atom probe investigation. Journal of Applied Physics, 2015, 117, .	2.5	7
60	Orientation and film thickness dependencies of (100)- and (111)-oriented epitaxial Pb(Mg1/3Nb2/3)O3 films grown by metal organic chemical vapor deposition. Journal of Materiomics, 2015, 1, 188-195.	5.7	3
61	Evaluation of oxygen vacancy in ZnO using Raman spectroscopy. , 2015, , .		13
62	Polar-axis-oriented crystal growth of tetragonal PZT films on stainless steel substrate using pseudo-perovskite nanosheet buffer layer. AIP Advances, 2015, 5, .	1.3	6
63	Effects of heat treatment on electrical and electromechanical properties of hydrothermally synthesized epitaxial (K <sub>0.51</sub> Na <sub>0.49</sub> )NbO <sub>3</sub> films. Japanese Journal of Applied Physics, 2014, 53, 05FE02.	1.5	7
64	Ferroelectric and piezoelectric properties of KNbO <sub>3</sub> films deposited on flexible organic substrate by hydrothermal method. Japanese Journal of Applied Physics, 2014, 53, 09PA10.	1.5	14
65	Structural and dielectric properties of BaTiO3–Bi(Mg1/2Ti1/2)O3thin films fabricated by chemical solution deposition. Japanese Journal of Applied Physics, 2014, 53, 09PA11.	1.5	4
66	Electrical Properties of (110)-Oriented Nondoped Mg2Si Films with p-Type Conduction Prepared by RF Magnetron Sputtering Method. Journal of Electronic Materials, 2014, 43, 2269-2273.	2.2	25
67	Lead- and alkali-metal-free BaTiO3–Bi(Mg0.5Ti0.5)O3–BiFeO3solid-solution thin films with high dielectric constant prepared on Si substrates by solution-based method. Japanese Journal of Applied Physics, 2014, 53, 09PA12.	1.5	4
68	Investigation of mixing effects of silicon isotopes under shaveâ€off condition using atom probe tomography. Surface and Interface Analysis, 2014, 46, 1200-1203.	1.8	1
69	HCM12A Cr-rich oxide layer investigation using 3D atom probe. Journal of Nuclear Materials, 2014, 450, 237-243.	2.7	4
70	Dielectric property of (001) one-axis oriented CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> -based thin films and their temperature dependence. Journal of the Ceramic Society of Japan, 2014, 122, 477-482.	1.1	2
71	Ferroelectric and piezoelectric properties of (K,Na)NbO3 thick films prepared on metal substrates by hydrothermal method. Journal of the Korean Physical Society, 2013, 62, 1055-1059.	0.7	19
72	Influence of lattice distortion and oxygen vacancies on the UV-driven/microwave-assisted TiO2 photocatalysis. Journal of Photochemistry and Photobiology A: Chemistry, 2013, 265, 20-28.	3.9	24

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73	Identification of the Occupation Site of Dy- or Y-Substituted PZT Films and the Correlation Between Occupation Site and Ferroelectric Property. Integrated Ferroelectrics, 2013, 141, 1-8.	0.7	1
74	One-Axis-Oriented Crystal Growth of Lead Zirconate Titanate Thin Films on Metal Substrates Using Perovskite-Type Oxide Nanosheet Layer. Key Engineering Materials, 2013, 582, 15-18.	0.4	1
75	Preparation of (La,Sr)MnO <sub>3</sub> Thin Film by Chemical Solution Deposition. Key Engineering Materials, 2013, 566, 187-190.	0.4	0
76	Three-Dimensional Dopant Characterization of Actual Metal–Oxide–Semiconductor Devices of 65 nm Node by Atom Probe Tomography. Applied Physics Express, 2013, 6, 046502.	2.4	11
77	Crystal Structure Analysis of Hydrothermally Synthesized Epitaxial (K <sub>x</sub> Na <sub>1-x</sub> )NbO <sub>3</sub> Films. Japanese Journal of Applied Physics, 2013, 52, 09KA11.	1.5	22
78	Unusual $90\hat{A}^{\circ}$ domain structure in $(2/3)$ Bi $(Zn1/2Ti1/2)$ O3- $(1/3)$ BiFeO3 epitaxial films with giant 22% tetragonal distortion. Applied Physics Letters, 2013, 103, .	3.3	8
79	Leakage current characteristics of new SrBi <inf>O<inf>15</inf>/CaBi<inf>4</inf>Ti<irthun-film ,="" .<="" 2013,="" capacitor="" electric="" excellent="" stability.="" td="" with=""><td>nf&gt;4&lt;</td><td>:/infl&gt;O&lt;</td></irthun-film></inf>	nf>4<	:/infl>O<
80	Composition dependency of crystal structure, electrical and piezoelectric properties for hydrothermally-synthesized 3 Aµm-thickness (K <i><sub>x</sub><td>&amp;g<del>1</del>;)NbO</td><td><sub>38</sub></td></i>	&g <del>1</del> ;)NbO	<sub>38</sub>
81	Fabrication and Evaluation of One-Axis Oriented Lead Zirconate Titanate Films Using Metal–Oxide Nanosheet Interface Layer. Japanese Journal of Applied Physics, 2013, 52, 09KA04.	1.5	11
82	Dielectric Property of Silicate-Doped CaBi\$_{4}\$Ti\$_{4}\$O\$_{15}\$ Thin Films. Japanese Journal of Applied Physics, 2012, 51, 09LA16.	1.5	1
83	A new SrBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> /CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> thin-film capacitor for excellent electric stability. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2012, 59, 1888-1893.	3.0	3
84	Development of novel Pb, Li, Na and K-free piezoelectric materials for Si-based MEMS application. , 2012, , .		0
85	Growth of (111)-oriented BaTiO3–Bi(Mg0.5Ti0.5)O3 epitaxial films and their crystal structure and electrical property characterizations. Journal of Applied Physics, 2012, 111, .	2.5	15
86	Solubility of titanium diisopropoxide bis(dipivaloylmethanate) complex in supercritical carbon dioxide and its effect on supercritical fluid deposition process. Journal of Supercritical Fluids, 2012, 66, 59-65.	3.2	18
87	Dielectric Property of Silicate-Doped CaBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Thin Films. Japanese Journal of Applied Physics, 2012, 51, 09LA16.	1.5	0
88	Investigation of SrBi <inf>4</inf> Ti <inf>4</inf> O <inf>15</inf> /CaBi <inf>4</inf> Ti <inf>4</inf> O <inf>15</inf> <td></td> <td>0</td>		0
89	Mechanism of Contact Resistance Reduction in Nickel Silicide Films by Pt Incorporation. IEEE Transactions on Electron Devices, 2011, 58, 3778-3786.	3.0	13
90	Growth of Epitaxial 100-Oriented KNbO\$_{3}\$–NaNbO\$_{3}\$ Solid Solution Films on (100)\$_{ext{c}}\$SrRuO\$_{3}\$\$parallel\$(100)SrTiO\$_{3}\$ by Hydrothermal Method and Their Characterization. Japanese Journal of Applied Physics, 2011, 50, 09ND11.	1.5	26

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91	A New SrBi <inf>4</inf> Ti <inf>4</inf> O <inf>15</inf> /CaBi <inf>4</inf> Ti <inf. ,="" .<="" 2011,="" apacitor="" electric="" excellent="" for="" stability.="" td=""><td>nf&gt;4&lt;</td><td>;/in<b>6</b>&gt;0&amp;t</td></inf.>	nf>4<	;/in <b>6</b> >0&t
92	Crystal Orientation Control of Bismuth Layer-Structured Dielectric Films Using Interface Layers of Perovskite-Type Oxides. Japanese Journal of Applied Physics, 2011, 50, 09NA04.	1.5	13
93	Crystal Orientation Control of Bismuth Layer-Structured Dielectric Films Using Interface Layers of Perovskite-Type Oxides. Japanese Journal of Applied Physics, 2011, 50, 09NA04.	1.5	6
94	Growth of Epitaxial 100-Oriented KNbO3–NaNbO3Solid Solution Films on (100)cSrRuO3â^¥(100)SrTiO3by Hydrothermal Method and Their Characterization. Japanese Journal of Applied Physics, 2011, 50, 09ND11.	1.5	10
95	Dispersion of barium titanate and strontium titanate nanocubes and their selective accumulations. Journal of the Ceramic Society of Japan, 2010, 118, 688-690.	1.1	4
96	Composition dependence of crystal structure and electrical properties for epitaxial films of Bi(Zn1/2Ti1/2)O3-BiFeO3 solid solution system. Journal of the Ceramic Society of Japan, 2010, 118, 659-663.	1.1	10
97	Pulsed-laser Irradiation of Carbonaceous Materials in AgNO3 Solution and Its Application to Preparing Silver-activated Carbon Electrodes. Chemistry Letters, 2010, 39, 561-563.	1.3	0
98	Growth of polar axis oriented tetragonal Pb(Zr,Ti)O3 films on CaF2 substrates with transparent (La0.07Sr0.93)SnO3. Journal of Crystal Growth, 2010, 312, 3127-3130.	1.5	0
99	MOCVD growth and characterization of BiFeO3–Bi(Zn1/2Ti1/2)O3 ferroelectric films. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2010, 173, 14-17.	3.5	7
100	Highly-ordered mesoporous titania thin films prepared via surfactant assembly on conductive indium–tin-oxide/glass substrate and its optical properties. Thin Solid Films, 2010, 518, 3169-3176.	1.8	31
101	Dielectric Properties of Highly (001)-Plane Oriented SrBi <sub>4</sub> Ti <sub>4</sub> O <sub>15</sub> Thin Films. Key Engineering Materials, 2010, 445, 131-134.	0.4	2
102	Crystal Structure and Dielectric Property of Bismuth Layer-Structured Dielectric Films withc-Axis Preferential Crystal Orientation. Japanese Journal of Applied Physics, 2010, 49, 09MA02.	1.5	16
103	Effect of Film Thickness and Crystal Orientation on the Constituent Phase in Epitaxial BiFeO <sub>3</sub> â€"BiCoO <sub>3</sub> Films Grown on SrTiO <sub>3</sub> Substrates. Japanese Journal of Applied Physics, 2010, 49, 09MB04.	1.5	12
104	Atom probe microscopy of three-dimensional distribution of silicon isotopes in Si28â°•Si30 isotope superlattices with sub-nanometer spatial resolution. Journal of Applied Physics, 2009, 106, .	2.5	32
105	Preparation of (001)-Oriented CaBi4Ti4O15and SrBi4Ti4O15Films Using LaNiO3Nucleation Layer on Pt-passivated Si Wafer. Japanese Journal of Applied Physics, 2009, 48, 09KA10.	1.5	9
106	Preparation of Barium Titanate and Strontium Titanate Nanocube Particles and their Accumulation Using Smart Glue. Key Engineering Materials, 2009, 421-422, 514-517.	0.4	21
107	One-axis Oriented CaBi4Ti4O15 and SrBi4Ti4O15 Films Prepared on Silicon Wafer by Chemical Solution Deposition Technique. Materials Research Society Symposia Proceedings, 2009, 1199, 54.	0.1	0
108	Raman spectroscopic study of aqueous alkali sulfate solutions at high temperature and pressure to yield precipitation. Journal of Supercritical Fluids, 2009, 49, 303-309.	3.2	16

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109	Low temperature deposition of titanium oxide containing thin films in trench features from titanium diisopropoxide bis(dipivaloylmethanate) in supercritical CO2. Journal of Supercritical Fluids, 2009, 50, 313-319.	3.2	19
110	Raman OH stretching frequency shifts in supercritical water and in O2- and acetone-aqueous solutions near the water critical point. Chemical Physics Letters, 2009, 477, 85-89.	2.6	10
111	Low strain sensitivity of the dielectric property of pyrochlore Bi–Zn–Nb–O films. Applied Physics Letters, 2008, 92, 182901.	3.3	11
112	Low-Temperature Processing of Sol-Gel Derived Metal Oxide Thin Films using Supercritical Carbon Dioxide Fluid. Materials Research Society Symposia Proceedings, 2008, 1113, 1.	0.1	1
113	Electrophoretic Deposition of Au Nanocrystals inside Perpendicular Mesochannels of TiO2. Chemistry of Materials, 2008, 20, 6029-6040.	6.7	35
114	Pt Segregation at the NiSi/Si Interface and a Relationship with the Microstructure of NiSi. Materials Research Society Symposia Proceedings, 2008, 1070, 1.	0.1	9
115	Contact resistance reduction of Pt-incorporated NiSi for continuous CMOS scaling & amp; #x223C; Atomic level analysis of Pt/B/As distribution within silicide films & amp; #x223C;., 2008,,.		8
116	Pulsed-laser Irradiation to Suspended Carbon Particles in Aqueous Silver Nitrate Solution. Chemistry Letters, 2008, 37, 818-819.	1.3	1
117	Analysis for crystal structure of Bi(Fe,Sc)O3 thin films and their electrical properties. Applied Physics Letters, 2007, 91, .	3.3	60
118	Probing intrinsic polarization properties in bismuth-layered ferroelectric films. Applied Physics Letters, 2007, 90, 112914.	3.3	21
119	Bi-based ferroelectric thin films with enhanced polarization by rare-earth modification. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
120	Preparation and characterization of Bi-perovskite oxide films for piezo applications. Applications of Ferroelectrics, IEEE International Symposium on, 2007, , .	0.0	0
121	Kinetic aspects of SCWO progress of solid organic substances. Chemical Engineering Science, 2007, 62, 5070-5073.	3.8	8
122	Single-phase Pb(Zn1/3Nb2/3)O3 thin films grown by metalorganic chemical vapor deposition: Effects of growth sequence and substrates. Journal of Crystal Growth, 2007, 298, 495-499.	1.5	2
123	Characterization of zinc-modified lithium tantalate thin films fabricated by chemical solution deposition method. Journal of Sol-Gel Science and Technology, 2007, 42, 265-269.	2.4	1
124	Crystal structure and ferroelectric properties of rare-earth substituted BiFeO3 thin films. Journal of Applied Physics, 2006, 100, 014106.	2.5	228
125	Visualized Kinetic Aspects of a Wood Block in Sub- and Supercritical Water Oxidation. Industrial & Engineering Chemistry Research, 2006, 45, 5885-5890.	3.7	9
126	A Novel Hydroxyapatite Fiber Mesh as a Carrier for Recombinant Human Bone Morphogenetic Protein-2 Enhances Bone Union in Rat Posterolateral Fusion Model. Spine, 2006, 31, 1194-1200.	2.0	45

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127	Morphology change under pulsed laser irradiation of carbon particles suspended in water. Carbon, 2006, 44, 3356-3358.	10.3	6
128	Strong Dependence on Thickness of Room-Temperature Dielectric Constant of (100)-Oriented Pb(Mg1/3Nb2/3)O3Epitaxial Films Grown by Metal Organic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, L1074-L1076.	1.5	2
129	Formation of BiFeO3–BiScO3Thin Films and Their Electrical Properties. Japanese Journal of Applied Physics, 2006, 45, 7321-7324.	1.5	14
130	Site Occupancy Analysis on the Enhancement in Dy-Substituted Pb(Zr,Ti)O3Film. Japanese Journal of Applied Physics, 2006, 45, 7548-7551.	1.5	9
131	Synthesis of Oxide Thin Films on Silicon Substrate Using Supercritical Carbon Dioxide Fluid. Key Engineering Materials, 2006, 320, 91-94.	0.4	2
132	Synthesis and Properties of Nd-Substituted Bismuth Titanate Polycrystalline Thin Films with a-/b-Axes Orientation. Key Engineering Materials, 2006, 301, 57-60.	0.4	2
133	Electrical Properties of Perovskite-Based Ferroelectric Thin Films Modified Using Rare-Earth Elements. Key Engineering Materials, 2006, 320, 49-52.	0.4	0
134	Polarization comparison of Pb(Zr,Ti)O3 and Bi4Ti3O12-based ferroelectrics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2005, 118, 23-27.	3.5	10
135	Ion Modification for Improvement of Electrical Properties of Perovskite-based Ferroelectric Thin Films Fabricated by Chemical Solution Deposition Method. Materials Research Society Symposia Proceedings, 2005, 902, 1.	0.1	0
136	Structural and Electrical Properties of Polycrystalline Bi4-xNdxTi3O12Ferroelectric Thin Films with in-Planec-Axis Orientations. Japanese Journal of Applied Physics, 2005, 44, L292-L294.	1.5	4
137	Low-Temperature Deposition of Polycrystalline Titanium Oxide Thin Film on Si Substrate Using Supercritical Carbon Dioxide Fluid. Japanese Journal of Applied Physics, 2005, 44, 1901-1906.	1.5	23
138	MOCVD Growth of Bi1.5Zn1.0Nb1.5O7(BZN) Epitaxial Thin Films and Their Electrical Properties. Japanese Journal of Applied Physics, 2005, 44, 6957-6959.	1.5	17
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140	Perovskite Single-Phase Growth of Epitaxial Pb(Zn1/3Nb2/3)O3Films by Alternative-Source-Gas-Introduced Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2005, 44, L1452-L1455.	1.5	5
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